

BRF65R800T

Rev.A Apr.-2025

/ Descriptions

TO-220F N 650V

N-CHANNEL 650V Super-Junction Power MOSFET in a TO-220F Plastic Package.

/ Features

$R_{DS(on)} \times Q_g$ 100%

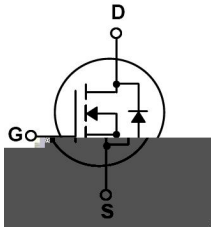
ROHS

Very low $R_{DS(on)} \times Q_g$, 100% avalanche tested, RoHS compliant, HF Product.

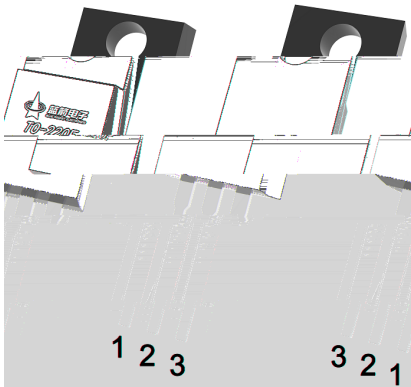
/ Applications

For switch mode power supply, uninterruptible power supply, power factor correction.

/ Equivalent Circuit



/ Pinning



PIN1 G

PIN 2 D

PIN 3 S

/ Marking

See Marking Instructions.

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DATA SHEET

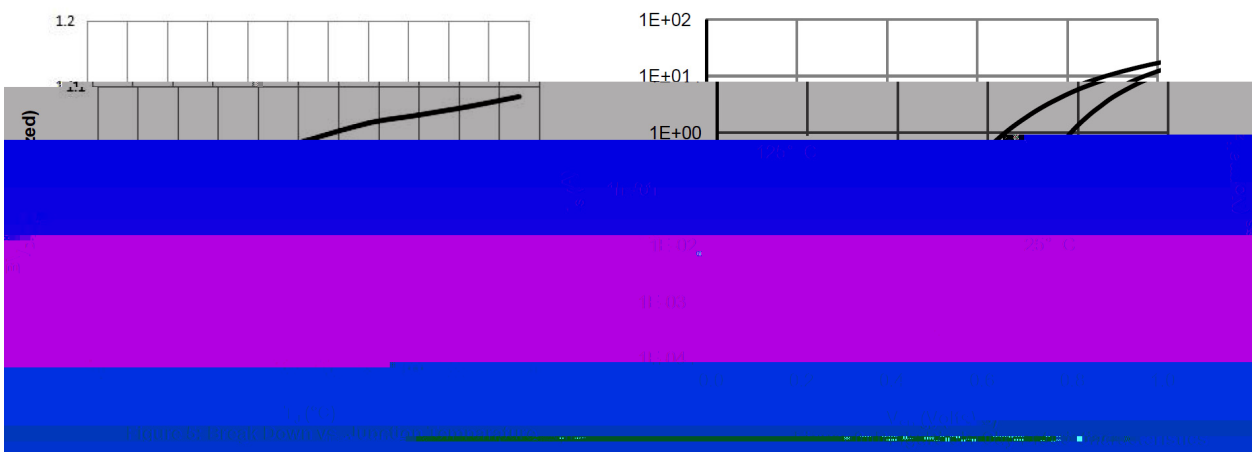
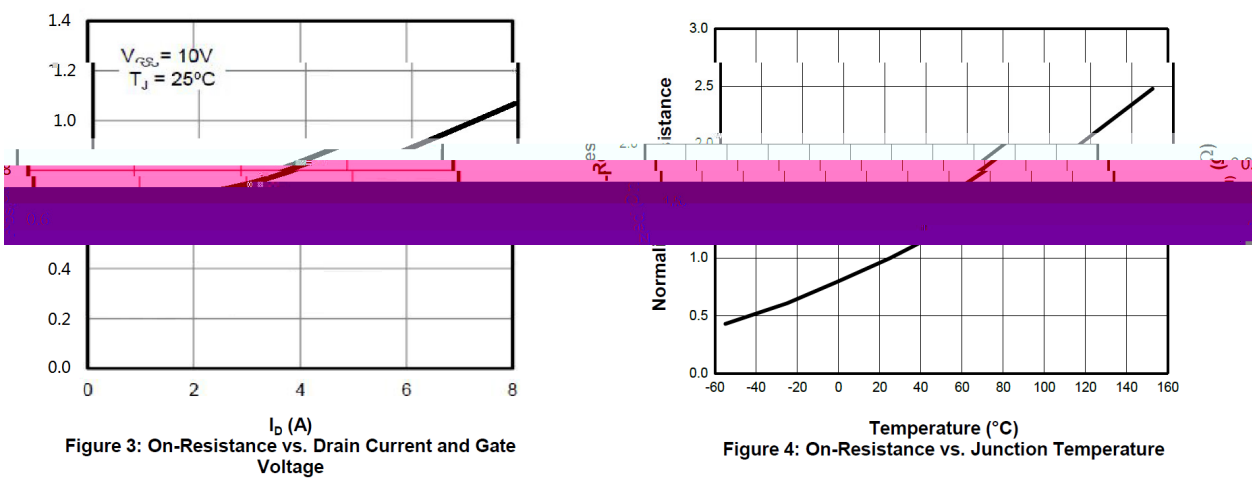
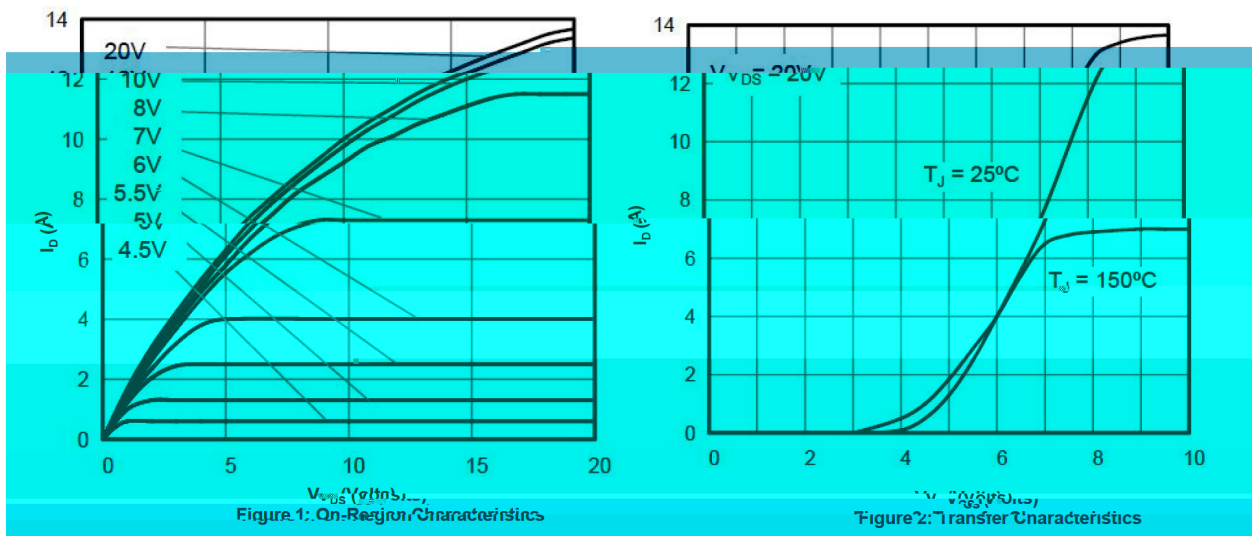
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	650	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	6	A
Drain Current - Pulsed	I_{DM}	24	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	146.5	mJ
Avalanche Current	I_{AS}	5.2	A
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	26	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	
Junction-to-Ambient	$R_{\theta JA}$	62.5	/W
Junction-to-Case	$R_{\theta JC}$	4.8	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\mu A$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V$ $V_{GS}=0V$ $T_J=25$			1.0	μA
Gate-Body Leakage Current, Forward	I_{GSS}	$V_{GS}=\pm 30V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.5		4.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=1.5A$		630	800	m Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_{SD}=1A$ $T_J=25$			1.3	V
Gate Resistance	R_g	$V_{GS}=0V$ $f=1.0MHz$		7.2		Ω
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		275		pF
Output Capacitance	C_{oss}			450		pF
Reverse Transfer Capacitance	C_{rss}			8		pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=400V$ $I_D=3A$ $V_{GS}=10V$ $R_G=25\Omega$		31.9		ns
Turn-On Rise Time	t_r			23.2		ns

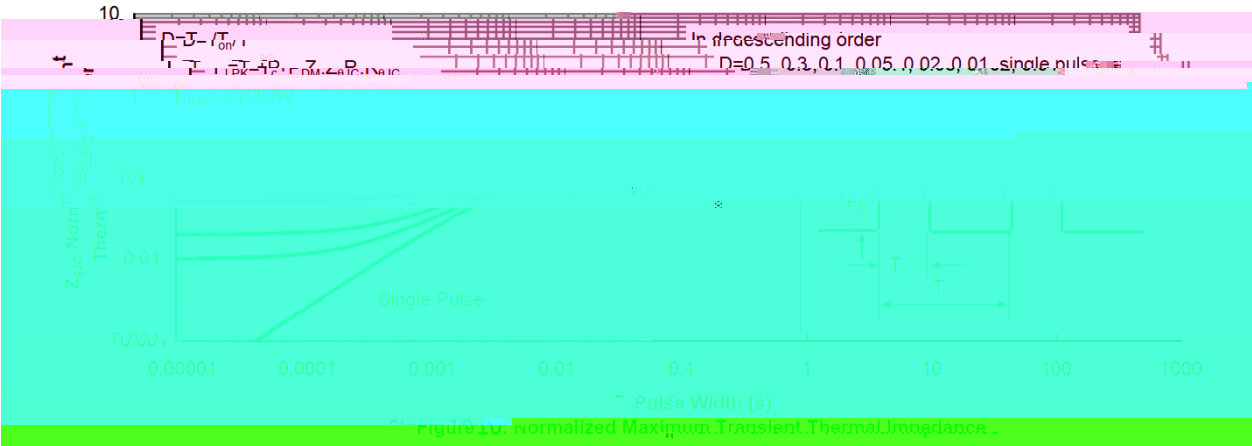
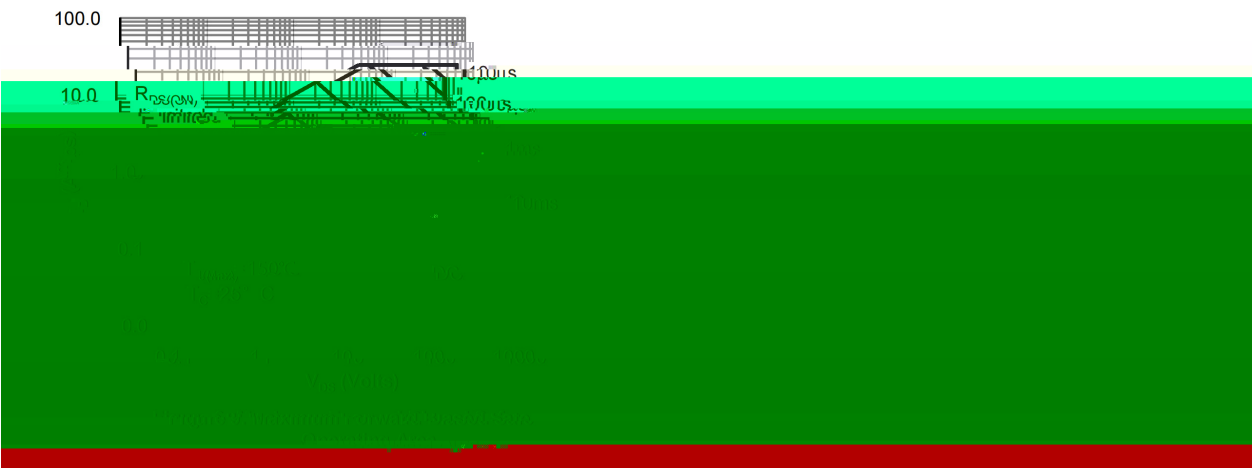
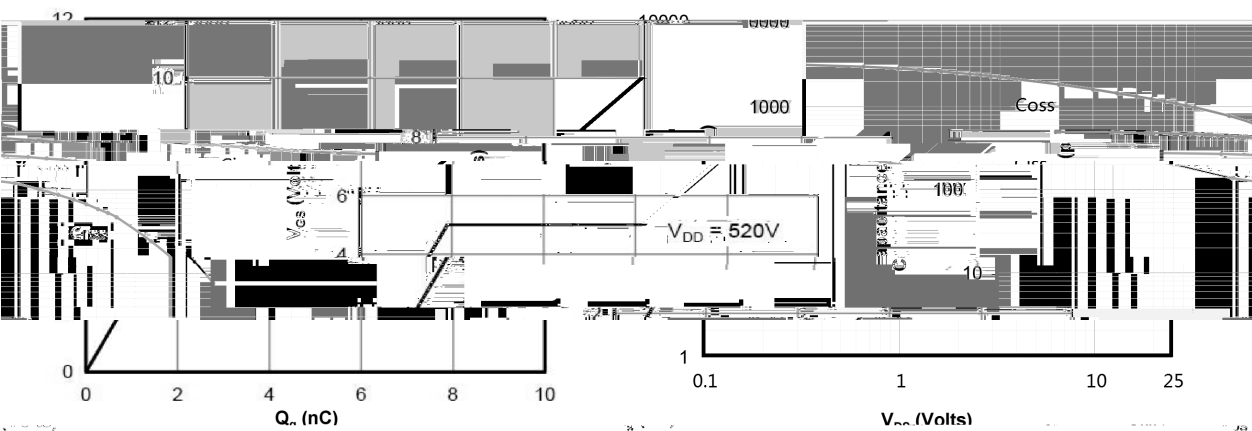
/ Electrical Characteristics(Ta=25)

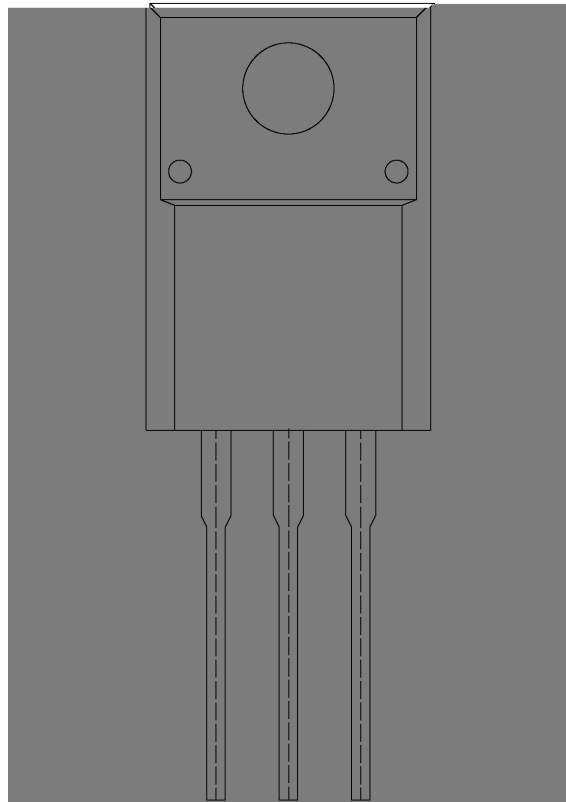
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous Diode Forward Current	I_S				6	A
Total Gate Charge	Q_g	$V_{DS}=520V \quad I_D=3A$ $V_{GS}=10V$		10.4		nC
Gate-Source Charge	Q_{gs}			2.5		nC
Gate-Drain Charge	Q_{gd}			2.0		nC
Reverse recovery time	T_{rr}	$V_R=400V \quad I_F=3A,$ $dI_F/dt=100 A/\mu s$		150		ns
Reverse recovery charge	Q_{rr}			1.06		uC

/ Electrical Characteristic Curve

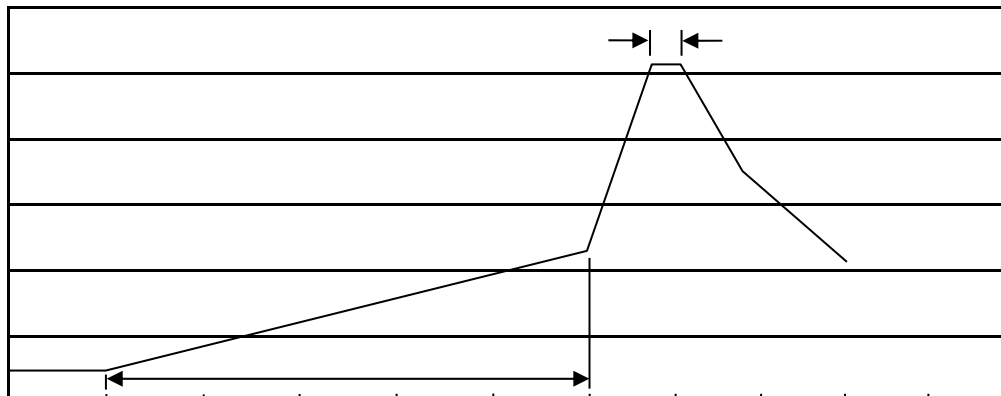


/ Electrical Characteristic Curve





() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1 25 150 60 90sec;
- 2 255±5 5±0.5sec;
- 3 2 10 /sec.

- 1.Preheating:25~150 , Time:60~90sec.
- 2.Peak Temp.:255±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm ³)		
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

/ Notices

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